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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	444
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe1500-2fg676i

1 – ProASIC3E Device Family Overview

General Description

ProASIC3E, the third-generation family of Microsemi flash FPGAs, offers performance, density, and features beyond those of the ProASIC^{PLUS}® family. Nonvolatile flash technology gives ProASIC3E devices the advantage of being a secure, low power, single-chip solution that is Instant On. ProASIC3E is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost. These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

ProASIC3E devices offer 1 kbit of on-chip, programmable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on six integrated phase-locked loops (PLLs). ProASIC3E devices have up to three million system gates, supported with up to 504 kbits of true dual-port SRAM and up to 620 user I/Os.

Several ProASIC3E devices support the Cortex-M1 soft IP cores, and the ARM-Enabled devices have Microsemi ordering numbers that begin with M1A3PE.

Flash Advantages

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based ProASIC3E devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property (IP) cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The ProASIC3E family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the ProASIC3E family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/ communications, computing, and avionics markets.

Security

The nonvolatile, flash-based ProASIC3E devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. ProASIC3E devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

ProASIC3E devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in ProASIC3E devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. The AES standard was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. ProASIC3E devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. ProASIC3E devices with AES-based security provide a high level of protection for secure, remote field updates over public networks such as the Internet, and ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the ProASIC3E family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The ProASIC3E family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3E device provides the best available security for programmable logic designs.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLXL exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see [Figure 2-1 on page 2-4](#) for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ($0.75\text{ V} \pm 0.25\text{ V}$), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *ProASIC3E FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

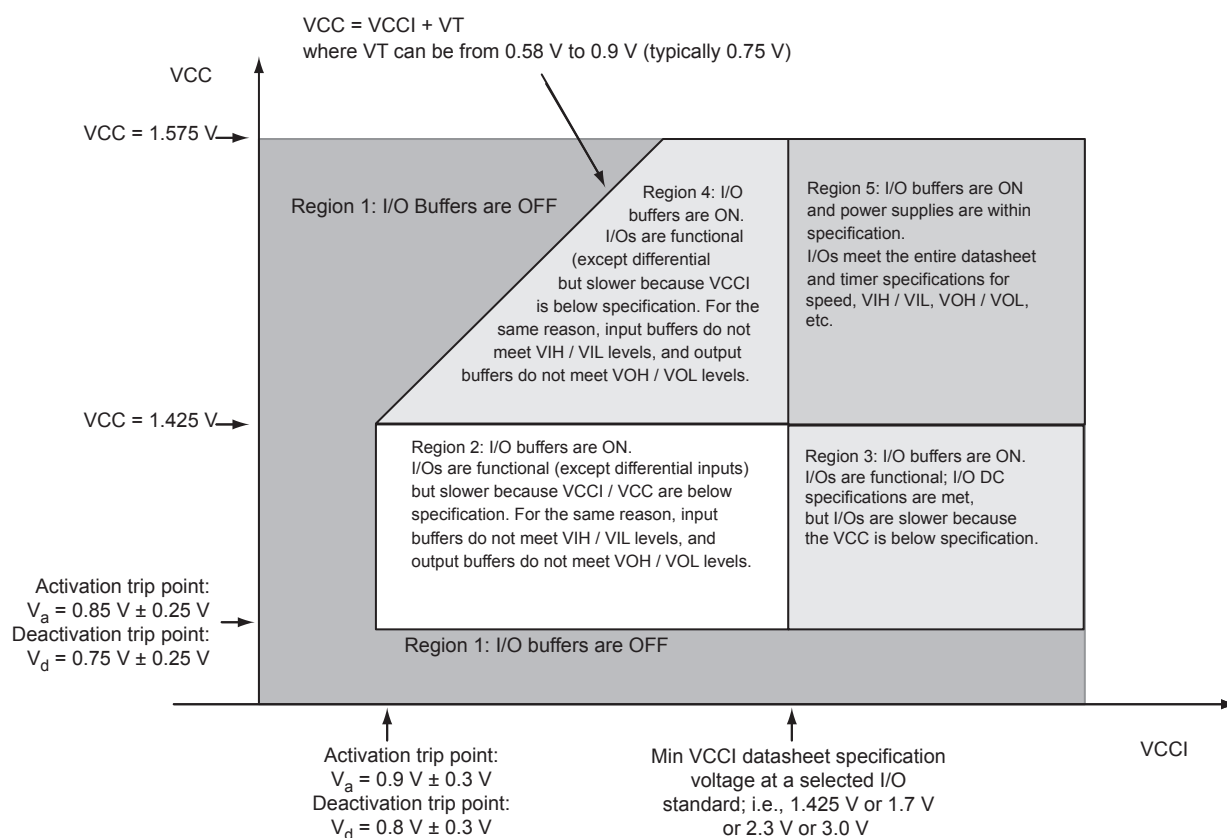


Figure 2-1 • I/O State as a Function of VCCI and VCC Voltage Levels

Table 2-8 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings (continued)

	VMV (V)	Static Power PDC2 (mW) ¹	Dynamic Power PAC9 (μW/MHz) ²
HSTL (I)	1.5	0.17	2.03
HSTL (II)	1.5	0.17	2.03
SSTL2 (I)	2.5	1.38	4.48
SSTL2 (II)	2.5	1.38	4.48
SSTL3 (I)	3.3	3.21	9.26
SSTL3 (II)	3.3	3.21	9.26
Differential			
LVDS/B-LVDS/M-LVDS	2.5	2.26	1.50
LVPECL	3.3	5.71	2.17

Notes:

1. PDC2 is the static power (where applicable) measured on VMV.
2. PAC9 is the total dynamic power measured on VCC and VMV.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8b specification.

Table 2-9 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings ¹

	C _{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW) ²	Dynamic Power PAC10 (μW/MHz) ³
Single-Ended				
3.3 V LVTTTL/LVCMOS	35	3.3	–	474.70
3.3 V LVTTTL/LVCMOS Wide Range ⁴	35	3.3	–	474.70
2.5 V LVCMOS	35	2.5	–	270.73
1.8 V LVCMOS	35	1.8	–	151.78
1.5 V LVCMOS (JESD8-11)	35	1.5	–	104.55
3.3 V PCI	10	3.3	–	204.61
3.3 V PCI-X	10	3.3	–	204.61
Voltage-Referenced				
3.3 V GTL	10	3.3	–	24.08
2.5 V GTL	10	2.5	–	13.52
3.3 V GTL+	10	3.3	–	24.10
2.5 V GTL+	10	2.5	–	13.54
HSTL (I)	20	1.5	7.08	26.22
HSTL (II)	20	1.5	13.88	27.22
SSTL2 (I)	30	2.5	16.69	105.56
SSTL2 (II)	30	2.5	25.91	116.60

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. PDC3 is the static power (where applicable) measured on VCCI.
3. PAC10 is the total dynamic power measured on VCC and VCCI.
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

Combinatorial Cells Contribution— P_{C-CELL}

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * PAC7 * F_{CLK}$$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-11 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

Routing Net Contribution— P_{NET}

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * PAC8 * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-11 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution— P_{INPUTS}

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * PAC9 * F_{CLK}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-11 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution— $P_{OUTPUTS}$

$$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * PAC10 * F_{CLK}$$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-11 on page 2-11](#).

β_1 is the I/O buffer enable rate—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

RAM Contribution— P_{MEMORY}

$$P_{MEMORY} = PAC11 * N_{BLOCKS} * F_{READ-CLOCK} * \beta_2 + PAC12 * N_{BLOCK} * F_{WRITE-CLOCK} * \beta_3$$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{READ-CLOCK}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations—guidelines are provided in [Table 2-12 on page 2-11](#).

$F_{WRITE-CLOCK}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in [Table 2-12 on page 2-11](#).

PLL Contribution— P_{PLL}

$$P_{PLL} = PAC13 + PAC14 * F_{CLKOUT}$$

F_{CLKOUT} is the output clock frequency.¹

1. The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($PAC14 * F_{CLKOUT}$ product) to the total PLL contribution.

Table 2-19 • I/O Output Buffer Maximum Resistances¹ (continued)

Standard	Drive Strength	R _{PULL-DOWN} (Ω) ²	R _{PULL-UP} (Ω) ³
3.3 V GTL+	35 mA	12	–
2.5 V GTL+	33 mA	15	–
HSTL (I)	8 mA	50	50
HSTL (II)	15 mA ⁴	25	25
SSTL2 (I)	15 mA	27	31
SSTL2 (II)	18 mA	13	15
SSTL3 (I)	14 mA	44	69
SSTL3 (II)	21 mA	18	32

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website at www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.
2. $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / IOL_{spec}$
3. $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / IOH_{spec}$
4. Output drive strength is below JEDEC specification.

Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

VCCI	R _(WEAK PULL-UP) ¹ (Ω)		R _(WEAK PULL-DOWN) ² (Ω)	
	Min.	Max.	Min.	Max.
3.3 V	10 k	45 k	10 k	45 k
3.3 V (Wide Range I/Os)	10 k	45 k	10 k	45 k
2.5 V	11 k	55 k	12 k	74 k
1.8 V	18 k	70 k	17 k	110 k
1.5 V	19 k	90 k	19 k	140 k

Notes:

1. $R_{(WEAK PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / I_{(WEAK PULL-UP-MIN)}$
2. $R_{(WEAK PULL-DOWN-MAX)} = (VOL_{spec}) / I_{(WEAK PULL-DOWN-MIN)}$

3.3 V LVCMOS Wide Range

Table 2-29 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Strength Option ¹	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	μA	μA	Max. mA ⁴	Max. mA ⁴	μA ⁵	μA ⁵
100 μA	2 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	27	25	10	10
100 μA	4 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	27	25	10	10
100 μA	6 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	54	51	10	10
100 μA	8 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	54	51	10	10
100 μA	12 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	109	103	10	10
100 μA	16 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	127	132	10	10
100 μA	24 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	181	268	10	10

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where −0.3 V < VIN < VIL.
3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.
4. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

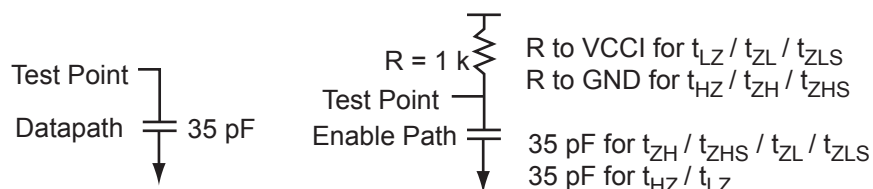


Figure 2-7 • AC Loading

Table 2-30 • 3.3 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	3.3	1.4	–	35

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Table 2-32 • 3.3 V LVCMOS Wide Range Low Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	4 mA	Std.	0.66	17.02	0.04	1.83	2.38	0.43	17.02	13.74	4.16	3.78	20.42	17.14	ns
		–1	0.56	14.48	0.04	1.55	2.02	0.36	14.48	11.69	3.54	3.21	17.37	14.58	ns
		–2	0.49	12.71	0.03	1.36	1.78	0.32	12.71	10.26	3.11	2.82	15.25	12.80	ns
100 μA	8 mA	Std.	0.66	12.16	0.04	1.83	2.38	0.43	12.16	9.78	4.70	4.74	15.55	13.17	ns
		–1	0.56	10.34	0.04	1.55	2.02	0.36	10.34	8.32	4.00	4.03	13.23	11.20	ns
		–2	0.49	9.08	0.03	1.36	1.78	0.32	9.08	7.30	3.51	3.54	11.61	9.84	ns
100 μA	12 mA	Std.	0.66	9.32	0.04	1.83	2.38	0.43	9.32	7.62	5.06	5.36	12.71	11.02	ns
		–1	0.56	7.93	0.04	1.55	2.02	0.36	7.93	6.48	4.31	4.56	10.81	9.37	ns
		–2	0.49	6.96	0.03	1.36	1.78	0.32	6.96	5.69	3.78	4.00	9.49	8.23	ns
100 μA	16 mA	Std.	0.66	8.69	0.04	1.83	2.38	0.43	8.69	7.17	5.14	5.53	12.08	10.57	ns
		–1	0.56	7.39	0.04	1.55	2.02	0.36	7.39	6.10	4.37	4.71	10.28	8.99	ns
		–2	0.49	6.49	0.03	1.36	1.78	0.32	6.49	5.36	3.83	4.13	9.02	7.89	ns
100 μA	24 mA	Std.	0.66	8.11	0.04	1.83	2.38	0.43	8.11	7.13	5.23	6.13	11.50	10.52	ns
		–1	0.56	6.90	0.04	1.55	2.02	0.36	6.90	6.06	4.45	5.21	9.78	8.95	ns
		–2	0.49	6.05	0.03	1.36	1.78	0.32	6.05	5.32	3.91	4.57	8.59	7.86	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

2.5 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

Table 2-51 • Minimum and Maximum DC Input and Output Levels

2.5 GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min., V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
20 mA ³	−0.3	VREF − 0.05	VREF + 0.05	3.6	0.4	−	20	20	124	169	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.
3. Output drive strength is below JEDEC specification.

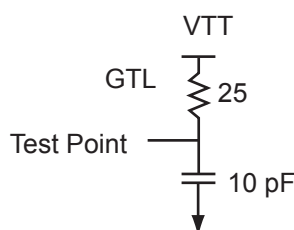


Figure 2-13 • AC Loading

Table 2-52 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF − 0.05	VREF + 0.05	0.8	0.8	1.2	10

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-53 • 2.5 V GTL

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.60	2.13	0.04	2.46	0.43	2.16	2.13			4.40	4.36	ns
−1	0.51	1.81	0.04	2.09	0.36	1.84	1.81			3.74	3.71	ns
−2	0.45	1.59	0.03	1.83	0.32	1.61	1.59			3.28	3.26	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

2.5 V GTL+

Gunning Transceiver Logic Plus is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

Table 2-57 • Minimum and Maximum DC Input and Output Levels

2.5 V GTL+	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
33 mA	−0.3	VREF − 0.1	VREF + 0.1	3.6	0.6	−	33	33	124	169	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.

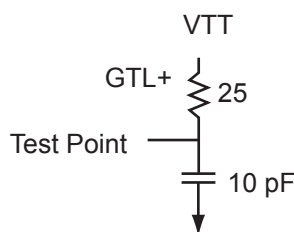


Figure 2-15 • AC Loading

Table 2-58 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF − 0.1	VREF + 0.1	1.0	1.0	1.5	10

Note: *Measuring point = Vtrip. See [Table 2-15 on page 2-18](#) for a complete table of trip points.

Timing Characteristics

Table 2-59 • 2.5 V GTL+

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 2.3 V, VREF = 1.0 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.60	2.21	0.04	1.51	0.43	2.25	2.10			4.48	4.34	ns
−1	0.51	1.88	0.04	1.29	0.36	1.91	1.79			3.81	3.69	ns
−2	0.45	1.65	0.03	1.13	0.32	1.68	1.57			3.35	3.24	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

HSTL Class II

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-63 • Minimum and Maximum DC Input and Output Levels

HSTL Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
15 mA ³	−0.3	VREF − 0.1	VREF + 0.1	3.6	0.4	VCCI − 0.4	15	15	55	66	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.
3. Output drive strength is below JEDEC specification.

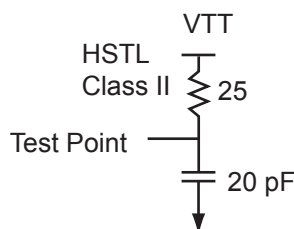


Figure 2-17 • AC Loading

Table 2-64 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF − 0.1	VREF + 0.1	0.75	0.75	0.75	20

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-65 • HSTL Class II

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.4 V, VREF = 0.75 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.66	3.02	0.04	2.12	0.43	3.08	2.71			5.32	4.95	ns
−1	0.56	2.57	0.04	1.81	0.36	2.62	2.31			4.52	4.21	ns
−2	0.49	2.26	0.03	1.59	0.32	2.30	2.03			3.97	3.70	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Output Register

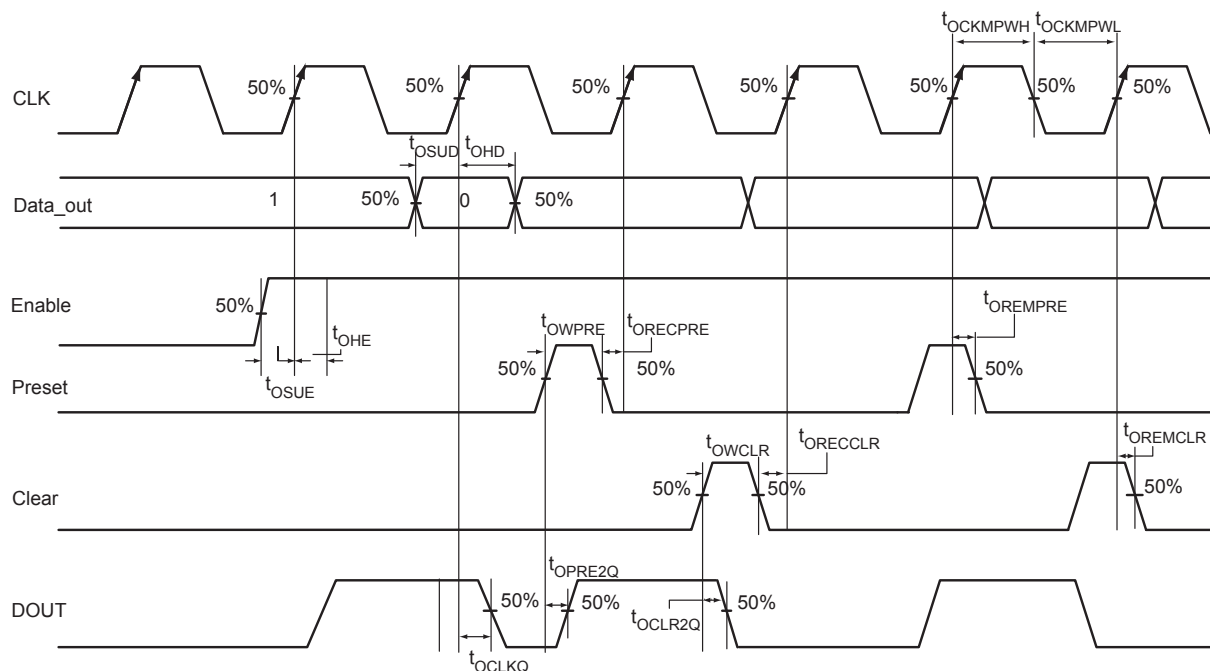


Figure 2-28 • Output Register Timing Diagram

Timing Characteristics

Table 2-87 • Output Data Register Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.59	0.67	0.79	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.31	0.36	0.42	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.44	0.50	0.59	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.80	0.91	1.07	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.80	0.91	1.07	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.36	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

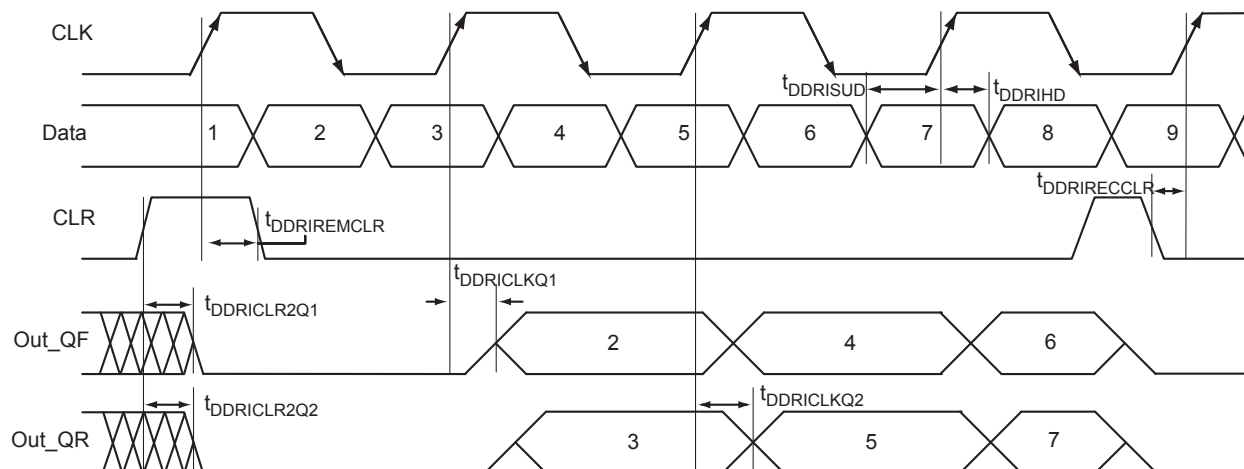


Figure 2-31 • Input DDR Timing Diagram

Timing Characteristics

Table 2-90 • Input DDR Propagation Delays

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DDRCLKQ1}	Clock-to-Out Out_QR for Input DDR	0.39	0.44	0.52	ns
t_{DDRCLKQ2}	Clock-to-Out Out_QF for Input DDR	0.27	0.31	0.37	ns
t_{DDRISUD}	Data Setup for Input DDR	0.28	0.32	0.38	ns
t_{DDRHD}	Data Hold for Input DDR	0.00	0.00	0.00	ns
$t_{\text{DDRCLR2Q1}}$	Asynchronous Clear to Out Out_QR for Input DDR	0.57	0.65	0.76	ns
$t_{\text{DDRCLR2Q2}}$	Asynchronous Clear to Out Out_QF for Input DDR	0.46	0.53	0.62	ns
$t_{\text{DDRREMCLR}}$	Asynchronous Clear Removal Time for Input DDR	0.00	0.00	0.00	ns
$t_{\text{DDRRECCLR}}$	Asynchronous Clear Recovery Time for Input DDR	0.22	0.25	0.30	ns
t_{DDRWCCLR}	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	0.25	0.30	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.36	0.41	0.48	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.32	0.37	0.43	ns
F_{DDRIMAX}	Maximum Frequency for Input DDR	1404	1232	1048	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

Timing Waveforms

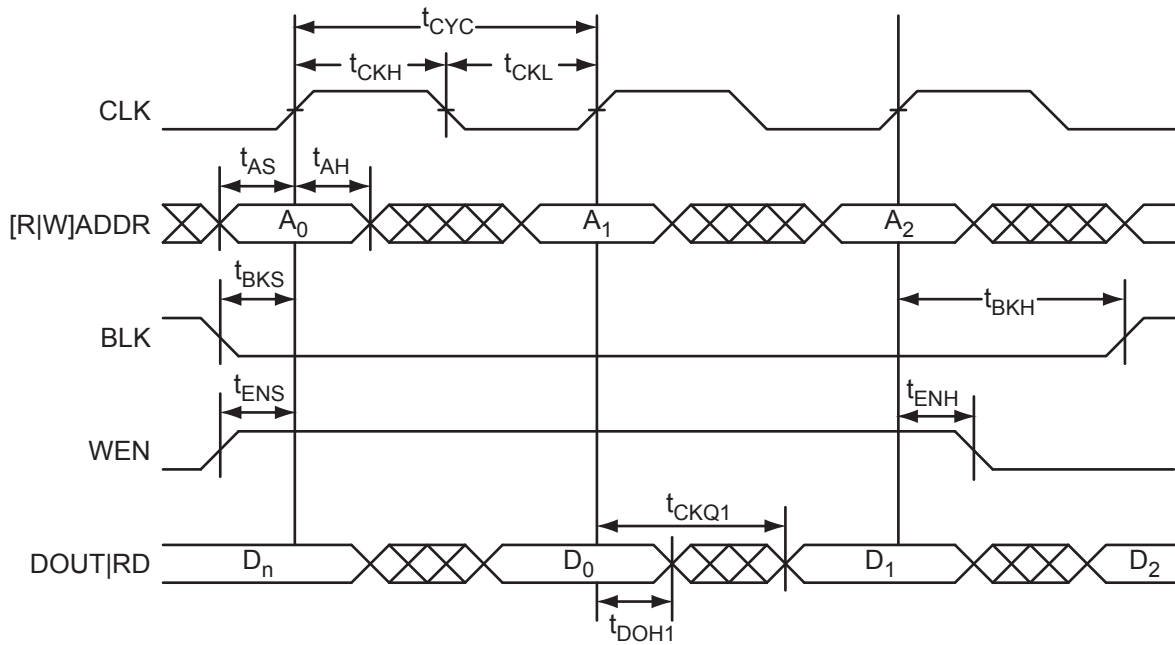


Figure 2-41 • RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.

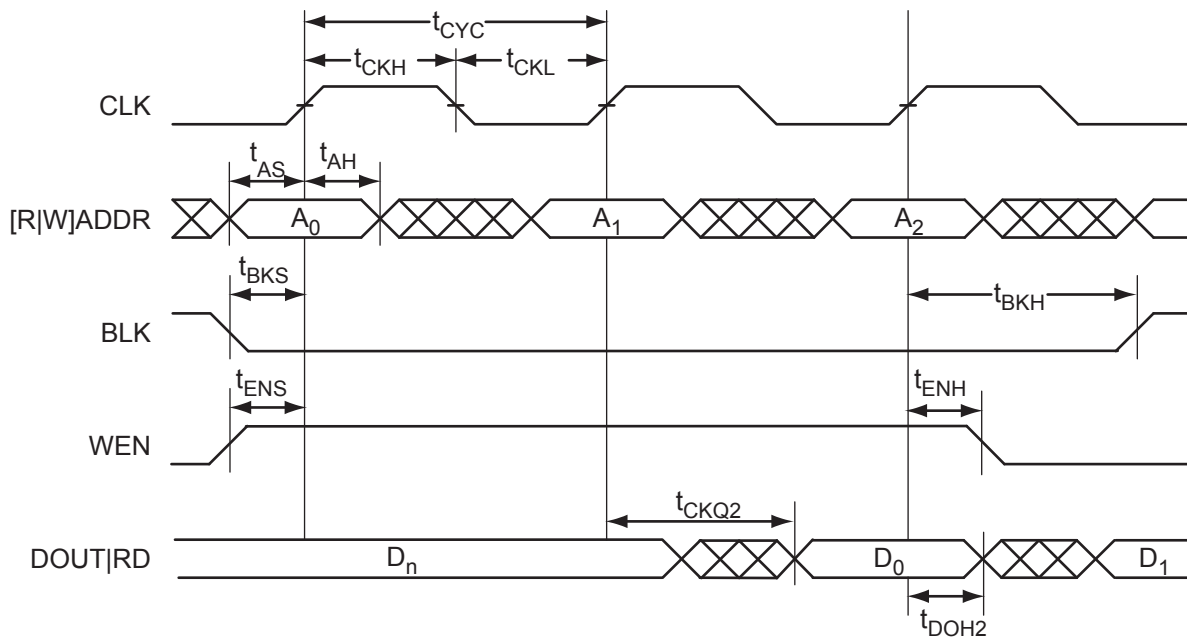


Figure 2-42 • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.

Timing Characteristics

Table 2-99 • RAM4K9

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{BKS}	BLK setup time	0.23	0.27	0.31	ns
t_{BKH}	BLK hold time	0.02	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	1.79	2.03	2.39	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
t_{C2CWWH}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.49	0.42	0.37	ns
t_{RSTBQ}	RESET Low to data out Low on DO (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DO (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

3 – Pin Descriptions and Packaging

Supply Pins

GND**Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ**Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC**Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx**I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. In general, unused I/O banks should have their corresponding VCCIX pins tied to GND. If an output pad is terminated to ground through any resistor and if the corresponding VCCIX is left floating, then the leakage current to ground is ~ 0uA. However, if an output pad is terminated to ground through any resistor and the corresponding VCCIX grounded, then the leakage current to ground is ~ 3 uA. For unused banks the aforementioned behavior is to be taken into account while deciding if it's better to float VCCIX of unused bank or tie it to GND.

VMVx**I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. x is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F**PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V.

When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the [ProASIC3E FPGA Fabric User's Guide](#) for a complete board solution for the PLL analog power supply and ground.

There are six VCCPLX pins on ProASIC3E devices.

VCOMPLA/B/C/D/E/F**PLL Ground**

Ground to analog PLL power supplies. When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

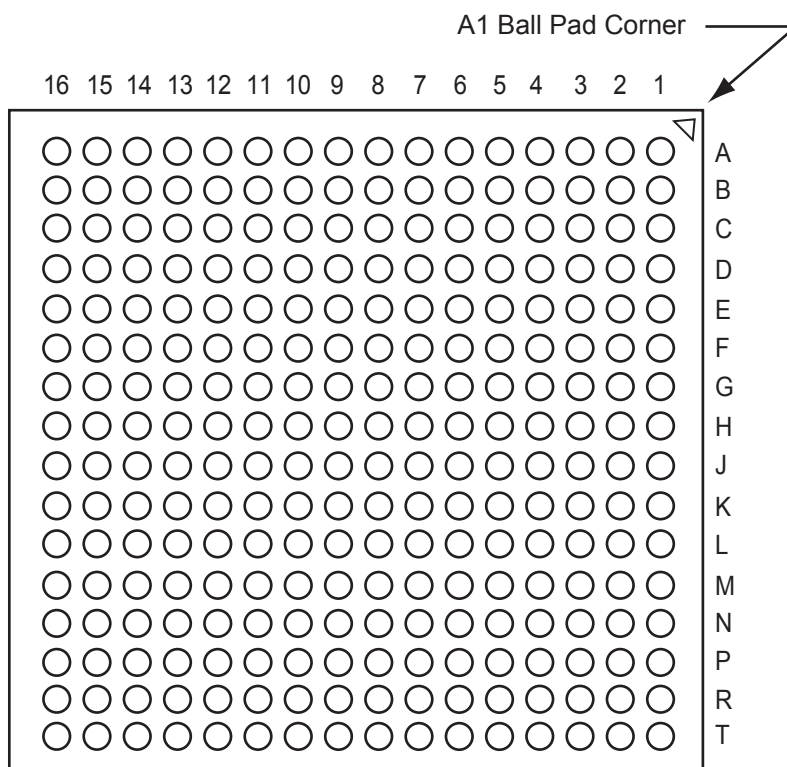
There are six VCOMPL pins (PLL ground) on ProASIC3E devices.

PQ208	
Pin Number	A3PE3000 Function
1	GND
2	GNDQ
3	VMV7
4	GAB2/IO308PSB7V4
5	GAA2/IO309PDB7V4
6	IO309NDB7V4
7	GAC2/IO307PDB7V4
8	IO307NDB7V4
9	IO303PDB7V3
10	IO303NDB7V3
11	IO299PDB7V3
12	IO299NDB7V3
13	IO295PDB7V2
14	IO295NDB7V2
15	IO291PSB7V2
16	VCC
17	GND
18	VCCIB7
19	IO285PDB7V1
20	IO285NDB7V1
21	IO279PSB7V0
22	GFC1/IO275PSB7V0
23	GFB1/IO274PDB7V0
24	GFB0/IO274NDB7V0
25	VCOMPLF
26	GFA0/IO273NPB6V4
27	VCCPLF
28	GFA1/IO273PPB6V4
29	GND
30	GFA2/IO272PDB6V4
31	IO272NDB6V4
32	GFB2/IO271PPB6V4
33	GFC2/IO270PPB6V4
34	IO271NPB6V4
35	IO270NPB6V4
36	VCC
37	IO252PDB6V2
38	IO252NDB6V2
39	IO248PSB6V1

PQ208	
Pin Number	A3PE3000 Function
40	VCCIB6
41	GND
42	IO244PDB6V1
43	IO244NDB6V1
44	GEC1/IO236PDB6V0
45	GEC0/IO236NDB6V0
46	GEB1/IO235PPB6V0
47	GEA1/IO234PPB6V0
48	GEB0/IO235NPB6V0
49	GEA0/IO234NPB6V0
50	VMV6
51	GNDQ
52	GND
53	VMV5
54	GNDQ
55	IO233NDB5V4
56	GEA2/IO233PDB5V4
57	IO232NDB5V4
58	GEB2/IO232PDB5V4
59	IO231NDB5V4
60	GEC2/IO231PDB5V4
61	IO230PSB5V4
62	VCCIB5
63	IO218NDB5V3
64	IO218PDB5V3
65	GND
66	IO214PSB5V2
67	IO212NDB5V2
68	IO212PDB5V2
69	IO208NDB5V1
70	IO208PDB5V1
71	VCC
72	VCCIB5
73	IO202NDB5V1
74	IO202PDB5V1
75	IO198NDB5V0
76	IO198PDB5V0
77	IO197NDB5V0
78	IO197PDB5V0

PQ208	
Pin Number	A3PE3000 Function
79	IO194NDB5V0
80	IO194PDB5V0
81	GND
82	IO184NDB4V3
83	IO184PDB4V3
84	IO180NDB4V3
85	IO180PDB4V3
86	IO176NDB4V2
87	IO176PDB4V2
88	VCC
89	VCCIB4
90	IO170NDB4V2
91	IO170PDB4V2
92	IO166NDB4V1
93	IO166PDB4V1
94	IO156NDB4V0
95	GDC2/IO156PDB4V0
96	IO154NPB4V0
97	GND
98	GDB2/IO155PSB4V0
99	GDA2/IO154PPB4V0
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV4
105	GND
106	VPUMP
107	GNDQ
108	TDO
109	TRST
110	VJTAG
111	VMV3
112	GDA0/IO153NPB3V4
113	GDB0/IO152NPB3V4
114	GDA1/IO153PPB3V4
115	GDB1/IO152PPB3V4
116	GDC0/IO151NDB3V4
117	GDC1/IO151PDB3V4

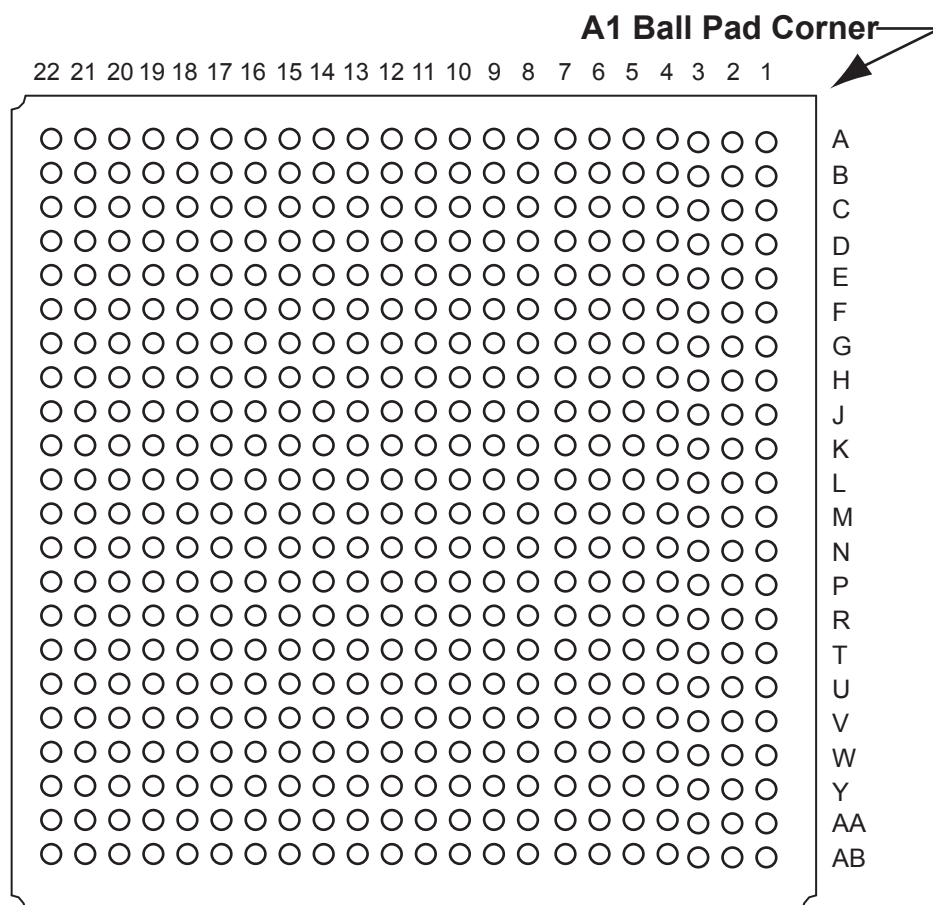
FG256



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.

FG484

Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.

FG896		FG896		FG896	
Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function
AG9	IO225NPB5V3	AH15	IO195NDB5V0	AJ21	IO173PDB4V2
AG10	IO223NPB5V3	AH16	IO185NDB4V3	AJ22	IO163NDB4V1
AG11	IO221PDB5V3	AH17	IO185PDB4V3	AJ23	IO163PDB4V1
AG12	IO221NDB5V3	AH18	IO181PDB4V3	AJ24	IO167NPB4V1
AG13	IO205NPB5V1	AH19	IO177NDB4V2	AJ25	VCC
AG14	IO199NDB5V0	AH20	IO171NPB4V2	AJ26	IO156NPB4V0
AG15	IO199PDB5V0	AH21	IO165PPB4V1	AJ27	VCC
AG16	IO187NDB4V4	AH22	IO161PPB4V0	AJ28	TMS
AG17	IO187PDB4V4	AH23	IO157NDB4V0	AJ29	GND
AG18	IO181NDB4V3	AH24	IO157PDB4V0	AJ30	GND
AG19	IO171PPB4V2	AH25	IO155NDB4V0	AK2	GND
AG20	IO165NPB4V1	AH26	VCCIB4	AK3	GND
AG21	IO161NPB4V0	AH27	TDI	AK4	IO217PPB5V2
AG22	IO159NDB4V0	AH28	VCC	AK5	GND
AG23	IO159PDB4V0	AH29	VPUMP	AK6	IO215PPB5V2
AG24	IO158PPB4V0	AH30	GND	AK7	GND
AG25	GDB2/IO155PDB4V0	AJ1	GND	AK8	IO207NDB5V1
AG26	GDA2/IO154PPB4V0	AJ2	GND	AK9	IO207PDB5V1
AG27	GND	AJ3	GEA2/IO233PPB5V4	AK10	IO201NDB5V0
AG28	VJTAG	AJ4	VCC	AK11	IO201PDB5V0
AG29	VCC	AJ5	IO217NPB5V2	AK12	IO193NDB4V4
AG30	IO149NDB3V4	AJ6	VCC	AK13	IO193PDB4V4
AH1	GND	AJ7	IO215NPB5V2	AK14	IO197PDB5V0
AH2	IO233NPB5V4	AJ8	IO213NDB5V2	AK15	IO191NDB4V4
AH3	VCC	AJ9	IO213PDB5V2	AK16	IO191PDB4V4
AH4	GEB2/IO232PPB5V4	AJ10	IO209NDB5V1	AK17	IO189NDB4V4
AH5	VCCIB5	AJ11	IO209PDB5V1	AK18	IO189PDB4V4
AH6	IO219NDB5V3	AJ12	IO203NDB5V1	AK19	IO179PPB4V3
AH7	IO219PDB5V3	AJ13	IO203PDB5V1	AK20	IO175NDB4V2
AH8	IO227NDB5V4	AJ14	IO197NDB5V0	AK21	IO175PDB4V2
AH9	IO227PDB5V4	AJ15	IO195PDB5V0	AK22	IO169NDB4V1
AH10	IO225PPB5V3	AJ16	IO183NDB4V3	AK23	IO169PDB4V1
AH11	IO223PPB5V3	AJ17	IO183PDB4V3	AK24	GND
AH12	IO211NDB5V2	AJ18	IO179NPB4V3	AK25	IO167PPB4V1
AH13	IO211PDB5V2	AJ19	IO177PDB4V2	AK26	GND
AH14	IO205PPB5V1	AJ20	IO173NDB4V2	AK27	GDC2/IO156PPB4V0

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-19 • I/O Output Buffer Maximum Resistances¹ and Table 2-21 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33853). 3.3 V LVCMOS Wide Range information was separated from regular 3.3 V LVCMOS and placed into its own new section, " 3.3 V LVCMOS Wide Range ". Values of IOSH and IOSL were added in Table 2-29 • Minimum and Maximum DC Input and Output Levels (SAR 33853).	2-20, 2-27
	The formulas in the table notes for Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 34755).	2-21
	The AC Loading figures in the " Single-Ended I/O Characteristics " section were updated to match tables in the " Summary of I/O Timing Characteristics – Default I/O Software Settings " section (SAR 34889).	2-24
	The titles and subtitles for Table 2-31 • 3.3 V LVCMOS Wide Range High Slew and Table 2-32 • 3.3 V LVCMOS Wide Range Low Slew were corrected (SAR 37227).	2-28, 2-29
	The following notes were removed from Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 34812): ±5% Differential input voltage = ±350 mV	2-50
	Minimum pulse width High and Low values were added to the tables in the " Global Tree Timing Characteristics " section. The maximum frequency for global clock parameter was removed from these tables because a frequency on the global is only an indication of what the global network can do. There are other limiters such as the SRAM, I/Os, and PLL. SmartTime software should be used to determine the design frequency (SAR 36957).	2-68
	A note was added to Table 2-98 • ProASIC3E CCC/PLL Specification indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34824).	2-70
	The following figures were deleted. Reference was made to a new application note, Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs , which covers these cases in detail (SAR 34872). Figure 2-44 • Write Access after Write onto Same Address Figure 2-45 • Read Access after Write onto Same Address Figure 2-46 • Write Access after Read onto Same Address The port names in the SRAM " Timing Waveforms ", SRAM " Timing Characteristics " tables, Figure 2-49 • FIFO Reset , and the FIFO " Timing Characteristics " tables were revised to ensure consistency with the software names (SAR 35750).	2-74, 2-75, 2-79, 2-82
	The " Pin Descriptions and Packaging " chapter is new (SAR 34771).	3-1
July 2010	Package names used in the " Package Pin Assignments " section were revised to match standards given in Package Mechanical Drawings (SAR 34771).	4-1
	Pin E6 for the FG256 package was corrected from VvB0 to VCCIB0 (SARs 30364, 31597, 26243).	4-9
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The " ProASIC3E Device Status " table on page II indicates the status for each device in the device family.	N/A